W SHANGHAI SUNRISE ELECTRONICS CO., LTD.

SB320 THRU SB360 SCHOTTKY BARRIER

RECTIFIER

TECHNICAL SPECIFICATION

VOLTAGE: 20 TO 60V CURRENT: 3.0A

FEATURES

- Epitaxial construction for chip
- High current capability
- Low forward voltage drop
- Low power loss, high efficiency
- High surge capability
- High temperature soldering guaranteed: 250°C/10sec/0.375"(9.5mm) lead length at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O recognized flame retardant epoxy
- Polarity: Color band denotes cathode
- Mounting position: Any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	SB 320	SB 330	SB 340	SB 350	SB 360	UNITS
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	20	30	40	50	60	V
Maximum RMS Voltage	V _{RMS}	14	21	28	35	42	V
Maximum DC Blocking Voltage	V _{DC}	20	30	40	50	60	V
Maximum Average Forward Rectified Curre	nt	3.0					А
(9.5mm lead length at $T_L=95^{\circ}C$)	^I F(AV)						
Peak Forward Surge Current (8.3ms single		80					Δ
half sine-wave superimposed on rated load)	IFSM						~
Maximum Forward Voltage (at 3.0A DC)	V _F	0.55 0.75			75	V	
Maximum DC Reverse Current T _a =25	°C _	3.0					mA
at rated DC blocking voltage T _a =100	°C ^{'R}	30					mA
Typical Junction Capacitance (Note	1) C _J	220					рF
Typical Thermal Resistance (Note	2) R _θ (ja)	30					°C/W
Operating Temperature	TJ	-(65 to +12	25	-65 tc	+150	°C
Storage Temperature	T _{STG}	-65 to +150					°C
Note:							

1.Measured at 1.0 MHz and applied reverse voltage of $4.0V_{dc}$

2. Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, vertical P.C. board mounted

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